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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROP.
K.N.	5,248,630	09/28/93	Serikawa et al.	437	101	03/26/92
K.N.	5,665,210	09/09/97	Yamazaki	438	3	05/27/94
K.N.	5,817,550	10/06/98	Carey et al.	438	166	03/05/96

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

## OTHER DOCUMENTS

Kav.	Article entitled, "Influence of $^{16}\text{O}$ , $^{12}\text{C}$ , $^{14}\text{N}$ , and Noble Gases on the Crystallization of Amorphous Si Layers", published in J. Appl. Phys., Vol. 48, by E. F. Kennedy et al., (1977), pp. 4241-4246
K.N.	Article entitled, "Microstructure of xenon-implanted silicon", published in J. Vac. Sci. Technol., Vol. 12, by S. Mader and K. N. Tu, (1975), pp. 501-503
K.N.	Article entitled, "Influence of Surface Absorption Characteristics on Reactively Sputtered Films Grown in the Biased and Unbiased Modes", by H. F. Winters and E. Kay, published in J. Appl. Phys., Vol. 43, No. 3, March 1972, pp. 794-799

EXAMINER

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